

1     ABSTRACT OF THE DISCLOSURE

2             Semiconductor processing methods of forming conductive projections  
3     and methods of increasing alignment tolerances are described. In one  
4     implementation, a conductive projection is formed over a substrate  
5     surface area and includes an upper surface and a side surface joined  
6     therewith to define a corner region. The corner region of the  
7     conductive projection is subsequently beveled to increase an alignment  
8     tolerance relative thereto. In another implementation, a conductive plug  
9     is formed over a substrate node location between a pair of conductive  
10    lines and has an uppermost surface. Material of the conductive plug  
11    is unevenly removed to define a second uppermost surface, at least a  
12    portion of which is disposed elevationally higher than a conductive line.  
13    In one aspect, conductive plug material can be removed by facet etching  
14    the conductive plug. In another aspect, conductive plug material is  
15    unevenly doped with dopant, and conductive plug material containing  
16    greater concentrations of dopant is etched at a greater rate than plug  
17    material containing lower concentrations of dopant.